

Serial No.:

Inventor(s): Becker et al.

METHOD FOR ENHANCING OXIDE TO NITRIDE SELECTIVITY
THROUGH THE USE OF INDEPENDENT HEAT CONTROL

ABSTRACT

INS
5 ~~1~~ A process for controlling the etch of a silicon dioxide layer at a high etch rate and high selectivity with respect to silicon nitride, particularly in a multilayer structure, by maintaining various portions of the etch chamber at elevated temperatures.

00923058.080601